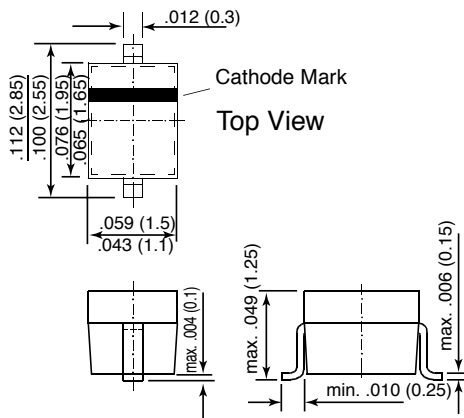


SD106WS

SCHOTTKY DIODES

SOD-323

Dimensions in inches and (millimeters)

FEATURES

- ◆ Low turn-on voltage
- ◆ Fast switching
- ◆ Microminiature plastic package
- ◆ These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- ◆ Ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications.

**MECHANICAL DATA****Case:** SOD-323 Plastic Package**Weight:** approx. 0.004g**Marking Code:** S2**MAXIMUM RATINGS**

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	VALUE	UNIT
Continuous Reverse Voltage	V_R	30	Volts
Forward Current	I_F	200	mA
Forward Surge Current, $t_p = 10\text{ms}$	I_{FSM}	1.0	A
Power Dissipation $T_C = 25^\circ\text{C}$	P_{tot}	250 (NOTE 1)	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to + 150	$^\circ\text{C}$

NOTES:

(1) Valid provided that electrodes are kept at ambient temperature

ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	MIN.	TYP.	MAX.	UNIT
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	BV_R	30	–	–	Volts
Leakage Current at $V_R = 30\ \text{V}$	I_R	–	–	5.0	μA
Forward Voltage					
at $I_F = 2.0\ \text{mA}$	V_F	–	260	–	mV
at $I_F = 15\ \text{mA}$	V_F	–	320	–	mV
at $I_F = 100\ \text{mA}$	V_F	–	420	–	mV
at $I_F = 200\ \text{mA}$	V_F	–	490	550	mV
Junction Capacitance at $V_R = 10\ \text{V}$, $f = 1.0\ \text{MHz}$	C_{tot}	–	–	Max 15	pF